



# BTA316B-800C

3Q Hi-Com Triac

Rev.03 - 30 July 2021

Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a TO263 (D2PAK) plastic package intended for use in circuits where high static and dynamic  $dV/dt$  and high  $dI/dt$  can occur. This "series C" triac will commute the full RMS current at the maximum rated junction temperature without the aid of a snubber.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by  $dV/dt$
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface mountable package
- Triggering in three quadrants only

## 3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Absolute maximum rating</b>						
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 101\text{ °C}$ <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	16	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	140	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	150	A
$T_j$	junction temperature		-	-	125	°C
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	2	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a>	2	-	35	mA

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$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	35	mA
$V_T$	on-state voltage	$I_T = 18\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	1.3	1.5	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit	500	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 16\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit	15	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA316B-800C	TO263	BTA316B-800C,118	Reel	800	TO263E (E)	26-May-2017
					TO263N (N)	26-Sep-2016

## 7. Marking

Table 4. Marking codes

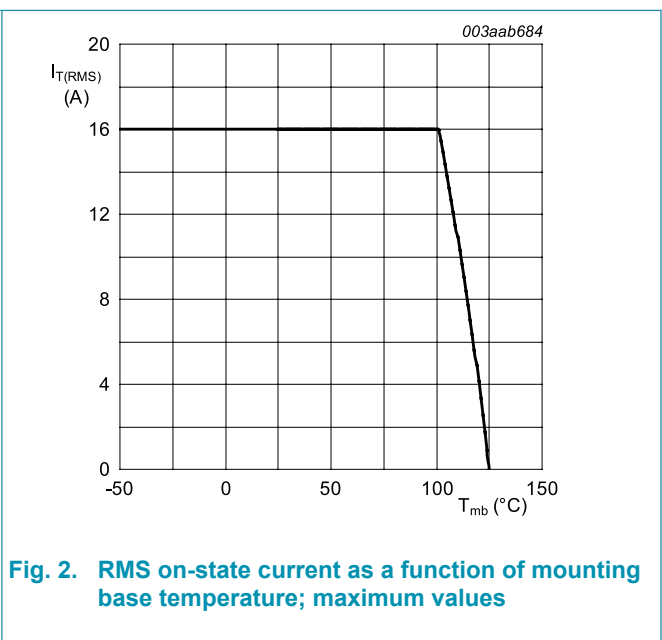
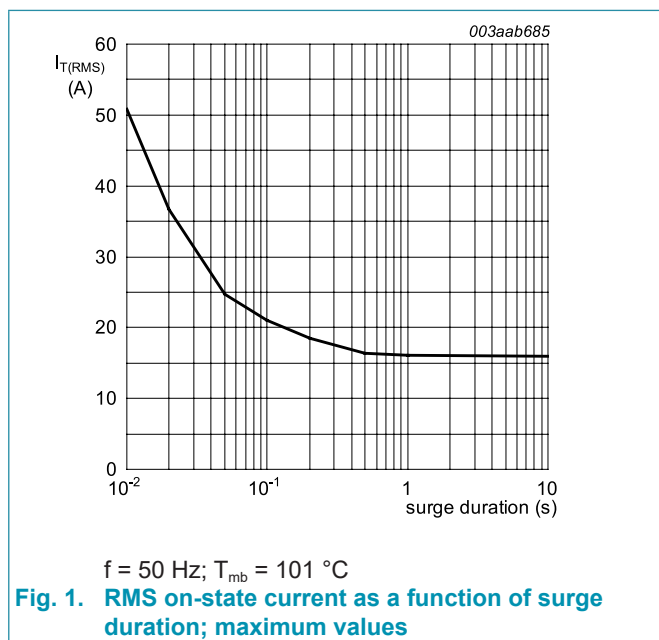
Type number	Marking codes	
	Assembly factory: E	Assembly factory: N
BTA316B-800C	BTA316B 800C PJExxxx xx	BTA316B 800C PJNxxxx xx

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 101\text{ °C}$ <a href="#">Fig 1</a> ; <a href="#">Fig 2</a> ; <a href="#">Fig 3</a>	-	16	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>	-	140	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	150	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; SIN	-	98	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	100	A/ $\mu$ s
$I_{GM}$	peak gate current		-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_{stg}$	storage temperature		-40	150	°C
$T_j$	junction temperature		-	125	°C



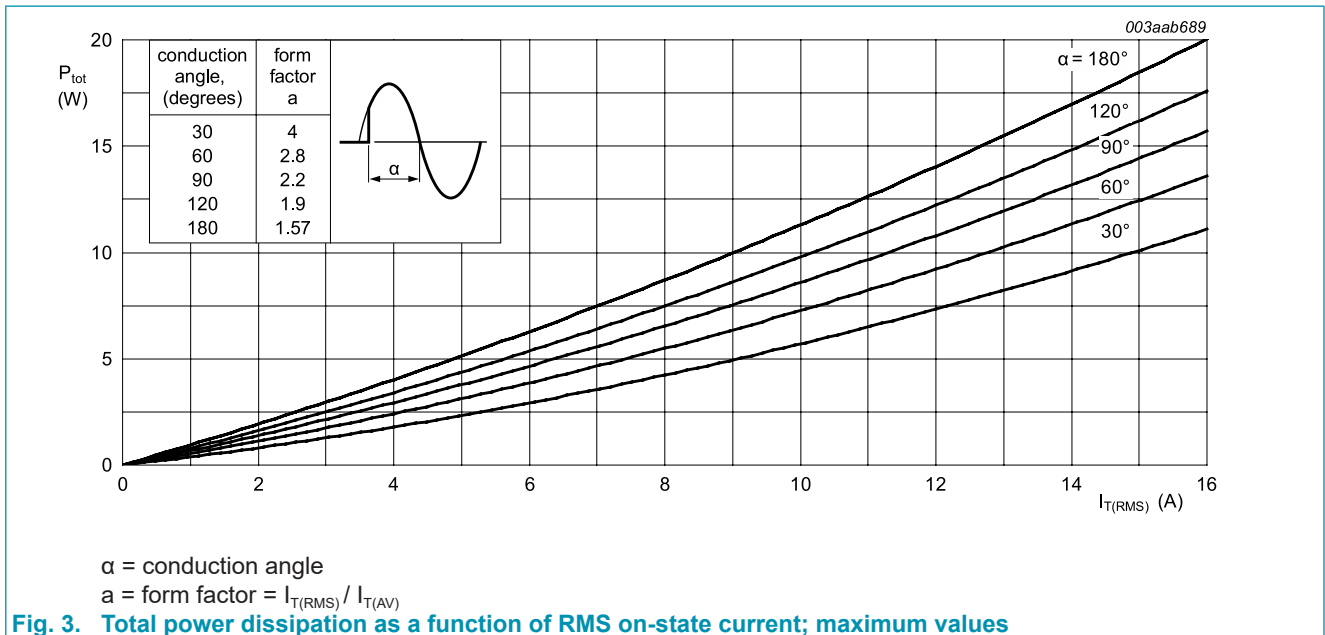


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

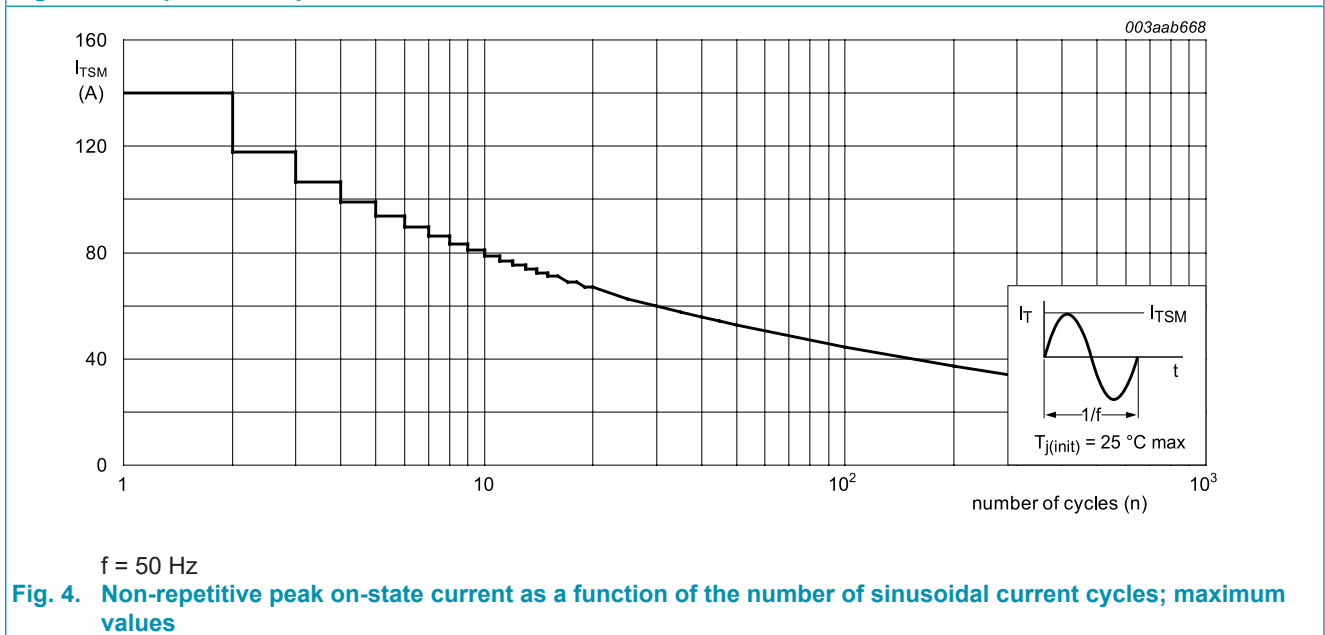
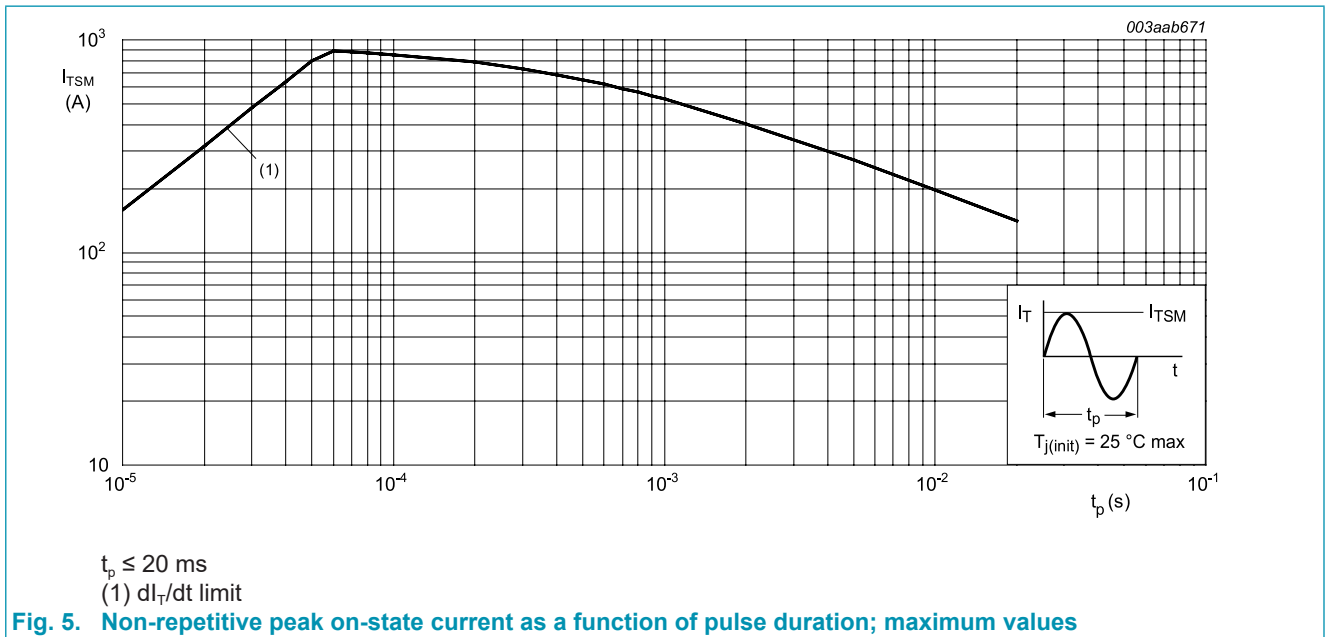


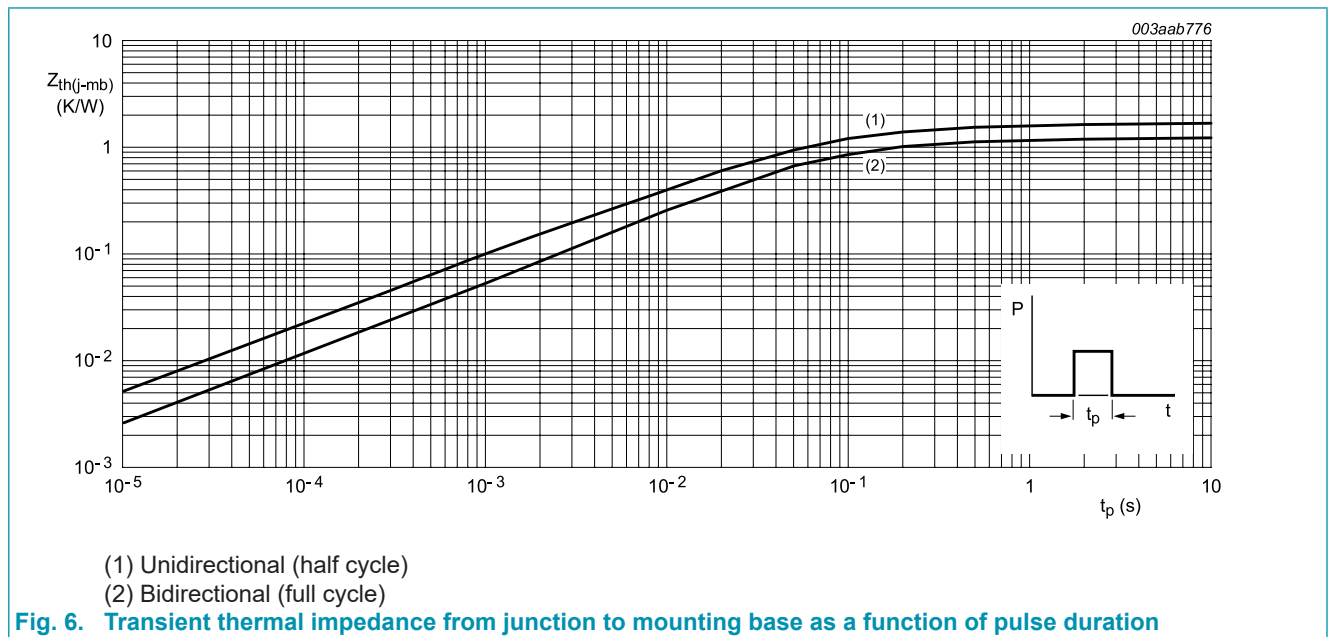
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 9. Thermal characteristics

Table 6. Thermal characteristics

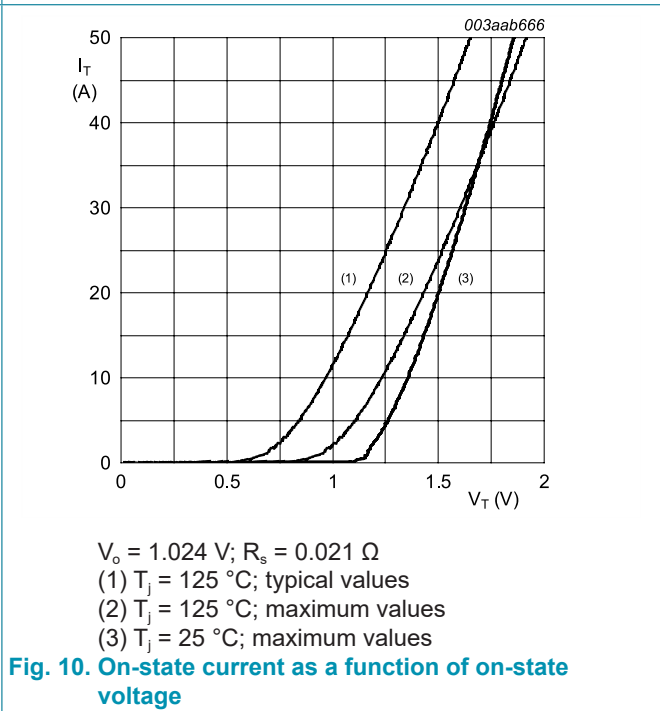
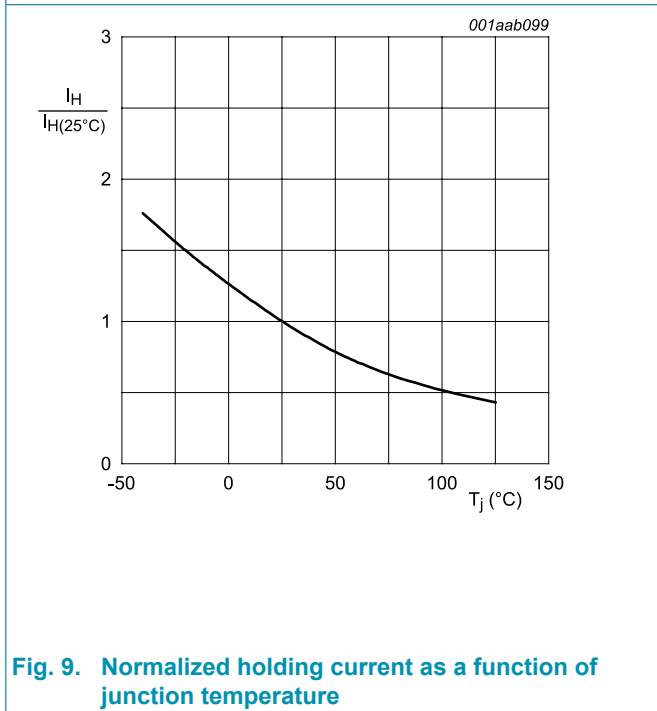
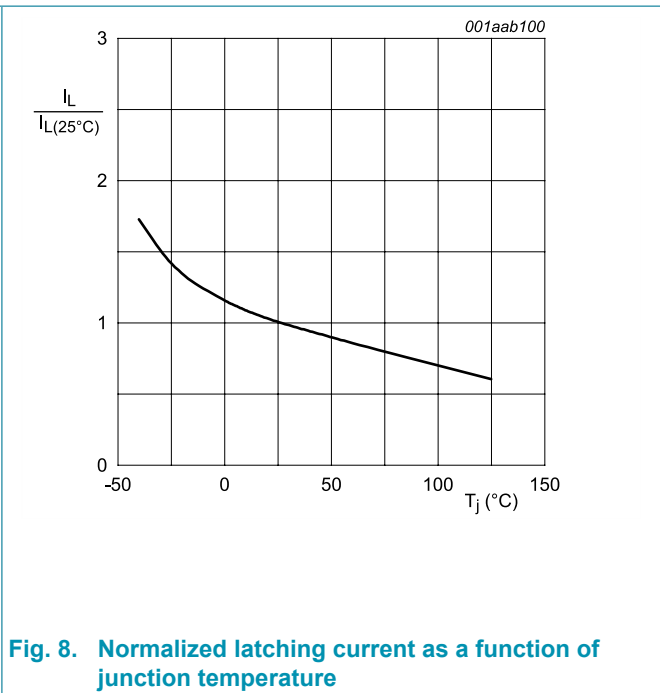
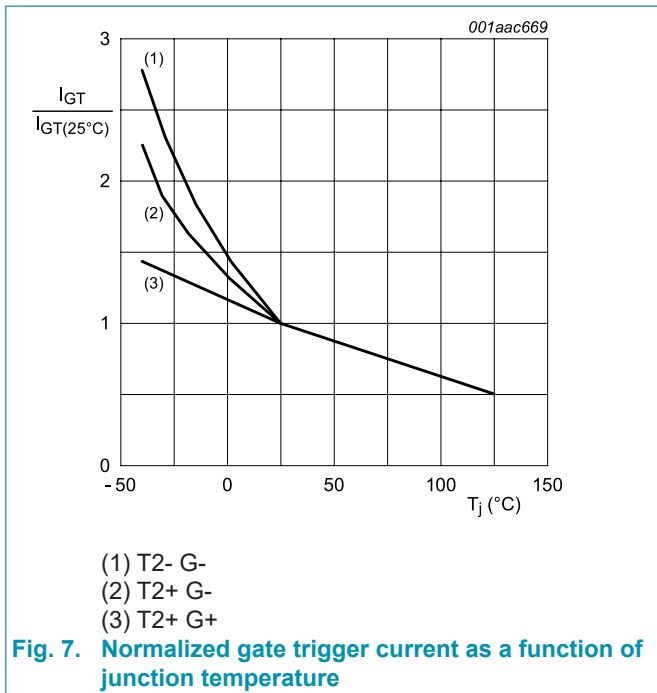
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig 6	-	-	1.2	K/W
		half cycle; Fig 6	-	-	1.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted; minimum footprint	-	55	-	K/W



## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	2	-	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	2	-	35	mA
		$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 7</a>	2	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G+;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	50	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2+ G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	60	mA
		$V_D = 12\text{ V}; I_G = 0.1\text{ A}; T_2- G-;$ $T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 8</a>	-	-	50	mA
$I_H$	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 9</a>	-	-	35	mA
$V_T$	on-state voltage	$I_T = 18\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 10</a>	-	1.3	1.5	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}; I_T = 0.1\text{ A}; T_j = 25\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	-	0.8	1	V
		$V_D = 400\text{ V}; I_T = 0.1\text{ A}; T_j = 125\text{ }^\circ\text{C};$ <a href="#">Fig. 11</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}; T_j = 125\text{ }^\circ\text{C}$	-	0.1	0.5	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}; T_j = 125\text{ }^\circ\text{C}; (V_{DM} = 67\%$ of $V_{DRM});$ exponential waveform; gate open circuit	500	-	-	V/ $\mu$ s
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}; T_j = 125\text{ }^\circ\text{C}; I_{T(RMS)} = 16\text{ A};$ $dV_{com}/dt = 20\text{ V}/\mu\text{s};$ (snubberless condition); gate open circuit	15	-	-	A/ms





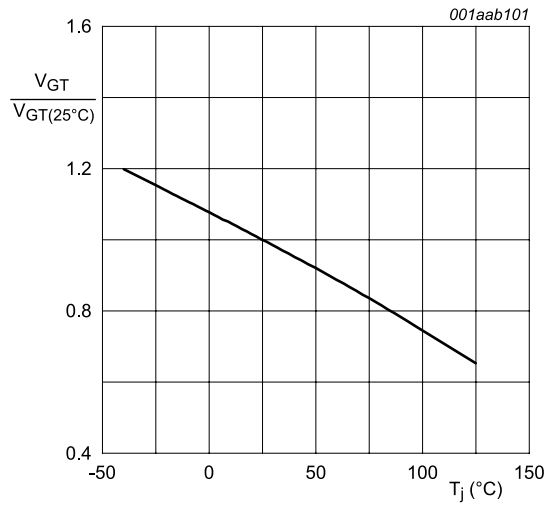
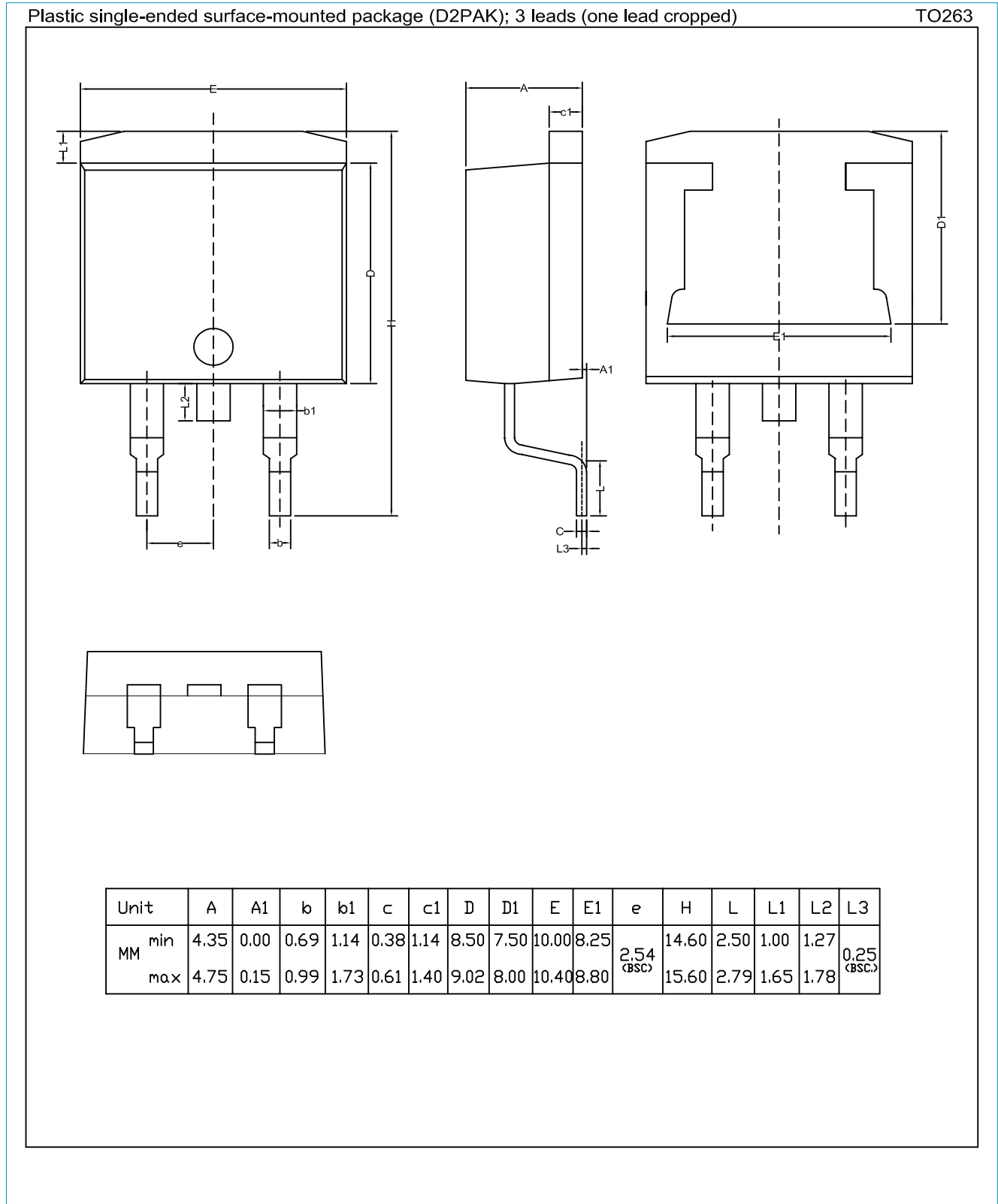


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

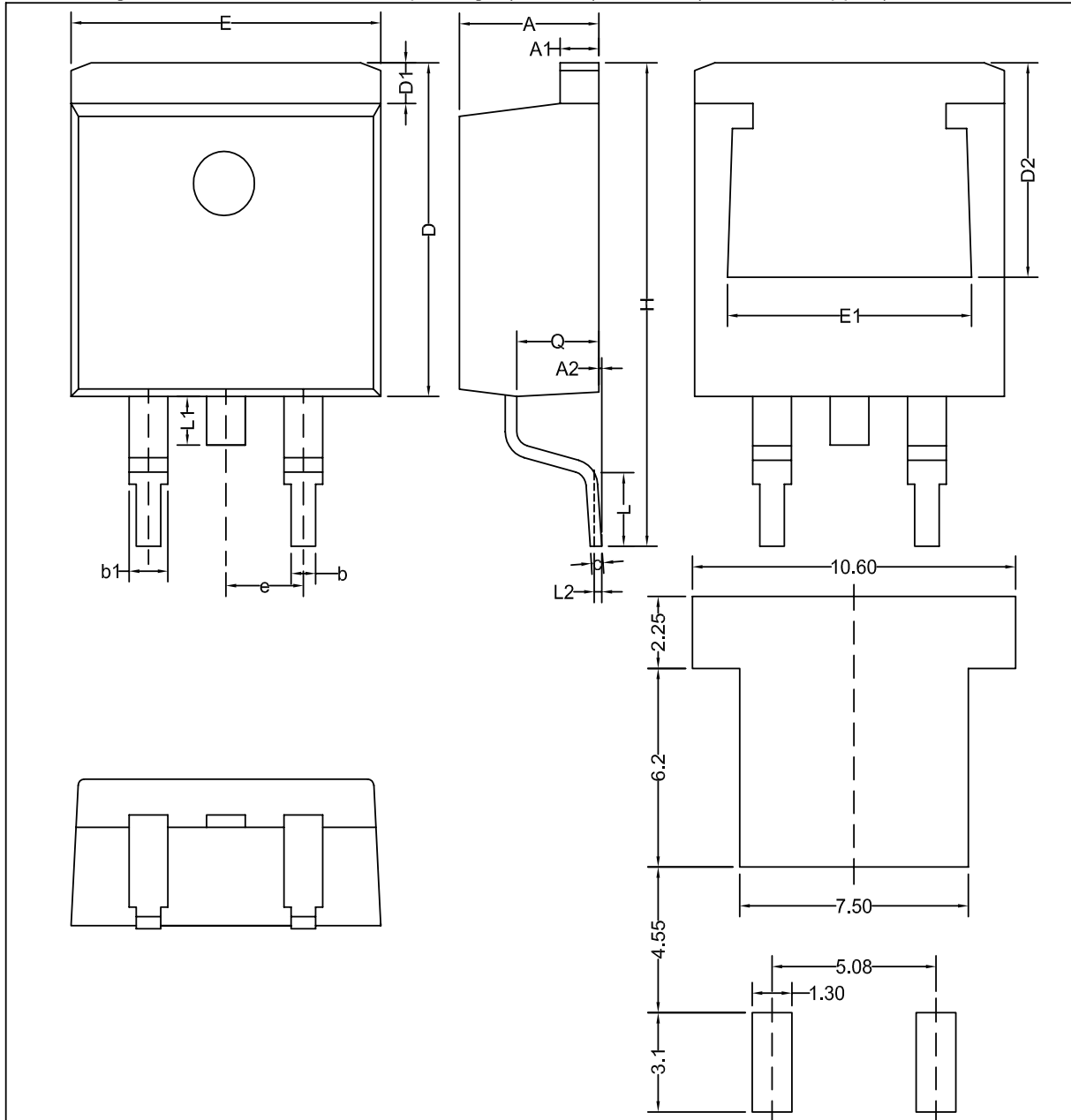
### 11. Package outline

Assembly factory: E



Assembly factory: N

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263



Recommended Footprint

Unit	A	A1	A2	b	b1	c	D	D1	D2	e	E	E1	H	L	L1	L2	Q
min	4.10	1.22	0.00	0.60	1.05	0.34	---	1.20	6.60	2.54 (BSC)	9.70	7.80	14.80	2.10	---	0.25 (BSC)	2.20
max	4.70	1.40	0.25	0.90	1.45	0.64	11.00	1.60	---	---	10.30	---	15.80	2.90	1.75	---	2.79

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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